

# Technical Data Sheet Opto Interrupter SGM8104

#### Features

- Fast response time
- High analytic
- Peak wavelength λp=940nm
- High sensitivity
- Pb free



### Descriptions

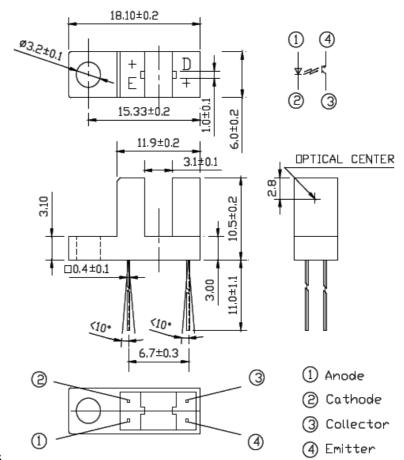
The SGM8104 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing. The phototransistor receives radiation from the IR LED only. This is the normal situation. But when an object is in between, phototransistor could not receives the radiation.

### Applications

- Non-contact Switching
- Switch Scanner
- For Direct Board
- Floppy disk driver



# **■** Package Dimensions



#### Notes:

- 1. All dimensions are in millimeters
- 2. Tolerances unless dimensions ±0.2mm
- 3. Lead spacing is measured where the lead emerge from the package

## Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	75	mW
	Reverse Voltage	$V_R$	5	V
	Forward Current	$I_{\mathrm{F}}$	50	mA
	Peak Forward Current (*1) Pulse width $\leq 100 \mu$ s, Duty cycle=1%	${ m I_{FP}}$	1	A
Output	Collector Power Dissipation	Pd	75	mW
	Collector Current	$I_{C}$	20	mA
	Collector-Emitter Voltage	$\mathrm{B}\mathrm{V}_{\mathrm{CEO}}$	30	V
	Emitter-Collector Voltage	$\mathrm{B}\mathrm{V}_{\mathrm{ECO}}$	5	V
Operating Temperature		Topr	-25~+85	℃
Storage Temperature		Tstg	-40~+85	℃
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	℃

(\*1) tw=100  $\mu$  sec. , T=10 msec. (\*2) t=5 Sec SHENZHEN SHUGUAN ELECTRONIC TECHNOLOGY CO.,LTD. V1.0 2010.07.03



## **Electro-Optical Characteristics (Ta=25°C)**

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	
	Forward Voltage	$V_{\mathrm{F}}$		1.2	1.5	V	$I_F=20mA$	
Input	Reverse Current	$I_R$			10	$\mu$ A	$V_R=5V$	
	Peak Wavelength	λр		940		nm	$I_F=20\text{mA}$	
	View Angle	201/2		60		Deg	I <sub>F</sub> =20mA	
	Dark C urrent	$I_{CEO}$			100	nA	$V_{CE}=20V,Ee=0mW/cm^2$	
Output	C-E Saturation Voltage	V <sub>CE</sub> (sat)			0.4	V	$I_C=2mA$	
							,Ee=1mW/cm <sup>2</sup>	
	Collect Current	I <sub>C</sub> (ON)	0.5		10	mA	$V_{CE}=5V$	
Transfer		Ic(OFF)			20	$\mu$ A	$I_F=20mA$	
Characteristics	Rise time	$t_{\rm r}$		15		$\mu$ sec	$V_{CE}=5V$	
	Fall time	$t_{\mathrm{f}}$		15		$\mu \sec$	$I_C=1 \text{mA}$	
							$R_L=1K\Omega$	

## Typical Electrical/Optical/Characteristics Curves for IR

Fig.1 Forward Current vs.

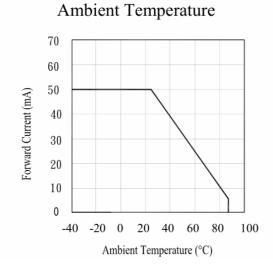


Fig.2 Spectral Distribution

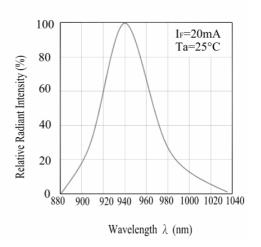


Fig.3 Peak Emission Wavelength vs. Ambient Temperature

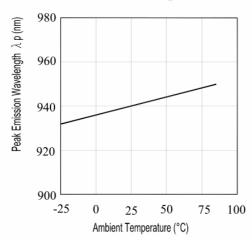


Fig.4 Forward Current

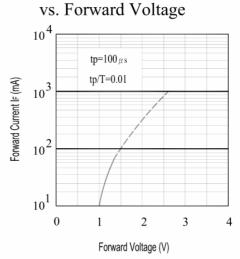


Fig.5 Forward Current vs Ambient Temperature(°C)

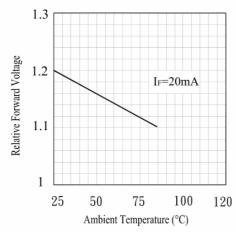
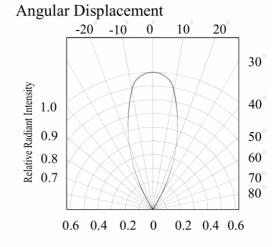


Fig.6 Relative Radiant Intensity vs.



# Typical Electrical/Optical/Characteristics Curves for PT

Fig.1Collector Power Dissipation vs.

Ambient Temperature

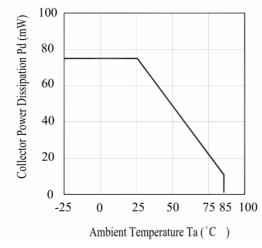


Fig.2 Spectral Sensitivity

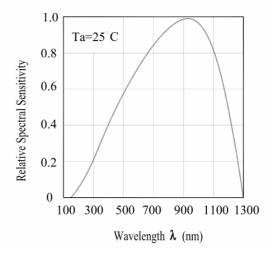


Fig.3 Relative Collector Current vs.



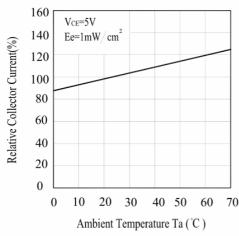


Fig.5 Collector Dark Current vs.

Ambient Temperature

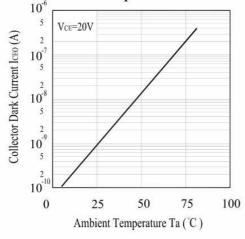


Fig.4 Collector Current vs.

#### Irradiance

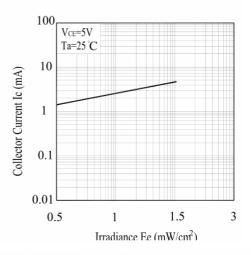
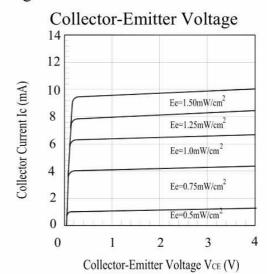


Fig.6 Collector Current vs.



## **■** Packing Quantity Specification

1. 100PCS/1Bag

#### Notes

- 1. Above specification may be changed without notice. SHUGUAN will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. SHUGUAN assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
- These specification sheets include materials protected under copyright of SHUGUAN corporation. Please don't reproduce or cause anyone to reproduce them without SHUGUAN's consent.